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**(54) THIN FILM SEMICONDUCTOR DEVICE,
ELECTRO-OPTICAL DEVICE, ELECTRONIC
INSTRUMENT AND MANUFACTURING
METHOD FOR THIN FILM SEMICONDUCTOR
DEVICE AND ELECTRO-OPTICAL DEVICE**

sitive resin 13 consists of a positive acrylic resin layer.

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(57) Abstract:

PROBLEM TO BE SOLVED: To provide a thin film semiconductor device, an electro-optical device, an electronic instrument and a manufacturing method for the thin film semiconductor device and the electro-optical device wherein dimensional precision is satisfied and both the enhancement of productivity and the reduction of material cost can be performed.

SOLUTION: An active matrix substrate 10 of a liquid crystal device has a first photosensitive resin 7 provided with a contact hole 7' and a second photosensitive resin 13 formed on the upper layer side of the layer of the first photosensitive resin and a contact hole 13' having the size smaller than the size of the contact hole 7' is formed in the position superposed on the contact hole 7' in the second photosensitive resin layer 13. The first photosensitive resin 7 consists of a negative acrylic resin layer and the second photosen-

